L	Hits	Search Text	DB	Time stamp
Number				
1	0	(variable adj resistane adj material) and	USPAT	2004/08/25
		memory and source and drain		09:37
2	3	(variable adj resistance adj material)	USPAT	2004/08/25
		and memory and source and drain		09:39
3	4	(variable adj resistance adj material)	US-PGPUB;	2004/08/25
		and memory and source and drain	EPO; JPO;	09:44
			DERWENT;	
			IBM_TDB	
4	182	, · · · · · · · · · · · · · · · · · · ·	US-PGPUB;	2004/08/25
		source and drain	EPO; JPO;	09:53
	ļ		DERWENT;	
			IBM_TDB	
5	552	(variable adj resistance) and memory and	USPAT	2004/08/25
		source and drain		10:22
6	139	source and drain and chalcogenide	USPAT	2004/08/25
		, , , , , , , , , , , , , , , , , , , ,		10:31
7	98	source and drain and chalcogenide	US-PGPUB;	2004/08/25
			EPO; JPO;	10:51
			DERWENT;	
			IBM_TDB	
8	9	pcram and memory	USPAT	2004/08/25
				10:54
9	69	pcram and memory	US-PGPUB;	2004/08/25
			EPO; JPO;	10:54
			DERWENT;	
			IBM_TDB	

L	Hits	Search Text	DB	Time stamp
Number				
1	0	(variable adj resistane adj material) and	USPAT	2004/08/25
2	3	memory and source and drain (variable adj resistance adj material)	USPAT	2004/08/25
3	4	(US-PGPUB;	09:39 2004/08/25
		and memory and source and drain	EPO; JPO; DERWENT; IBM TDB	09:44
4	182	(variable adj resistance) and memory and source and drain	US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 09:53
5	552	(variable adj resistance) and memory and source and drain	IBM_TDB USPAT	2004/08/25 09:53